

SANYO

No.2310A

LA7311**VTR-Use PAL/SECAM Discriminator
S-VHS Discriminator**

The LA7311 is a PAL/SECAM discriminator and S-VHS discriminator IC. When used as PAL/SECAM discriminator, the LA7311 is highly resistant to noise and is capable of providing high sensitive discrimination, because it uses the FM demodulation, peak detection method. Further, the LA7311 uses very few external parts, making the space-saving and low-cost discrimination block available, because it requires neither ceramic filter nor resonance coil. When used as S-VHS discriminator, the LA7311 is also capable of providing high sensitive discrimination.

Features

- Highly resistant to noise and burst input level variations and capable of providing high sensitive discrimination.
- Fewer external parts required (Neither ceramic filter nor resonance coil required)
- On-chip display LED drivers
- The polarity of burst gate pulse may be either positive or negative.

Absolute Maximum Ratings at Ta = 25°C

			unit
Maximum Supply Voltage	V_{CCmax}	7.0	V
Allowable Power Dissipation	P_{dmax}	130	mW
Operating Temperature	T_{opr}	-10 to +70	°C
Storage Temperature	T_{stg}	-40 to +125	°C

Operating Conditions at Ta = 25°C

			unit
Recommended Supply Voltage	V_{CC}	5.0	V
Operating Voltage Range	V_{CCop}	4.5 to 6.0	V

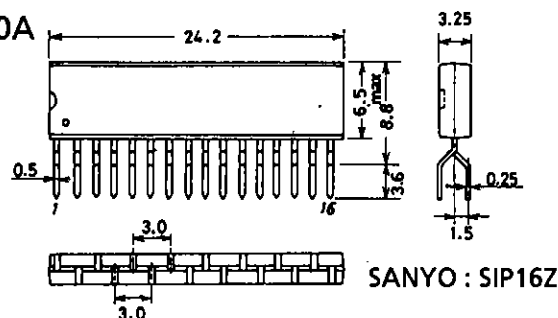
Operating Characteristics at Ta=25°C, $V_{CC}=5V$

			min	typ	max	unit
Current Dissipation	I_{CC}		6.7	9.6	12.4	mA
F-V Conversion Gain (PB)	ΔV_P	Difference between output at 4.4MHz and output at 4.25MHz	75	105	135	mV
F-V Conversion Gain (REC)	ΔV_R	Difference between output at 4.4MHz and output at 4.25MHz	75	105	135	mV
PAL → SECAM Inversion Voltage Difference	V_{8-12}		35	50	65	mV
R/P Switching Threshold Voltage	V_{3TH}		2.0	2.35	2.7	V
BG Threshold Voltage I	V_{7TH}		1.5	1.7	1.9	V
BG Threshold Voltage II	V_{11TH}		3.2	3.4	3.6	V
Forced PAL Threshold Voltage	V_{10TH}		1.3	1.7	2.2	V
Forced SECAM Threshold Voltage	V_{2TH}		1.7	2.0	2.3	V
Discrimination Output Voltage I	V_{13}	$I_D=5mA$	4.0	4.2	4.4	V
Discrimination Output Voltage II	V_{15}	$I_D=5mA$	4.0	4.2	4.4	V

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Package Dimensions 3020A

(unit: mm)

**SANYO Electric Co., Ltd. Semiconductor Business Headquarters**

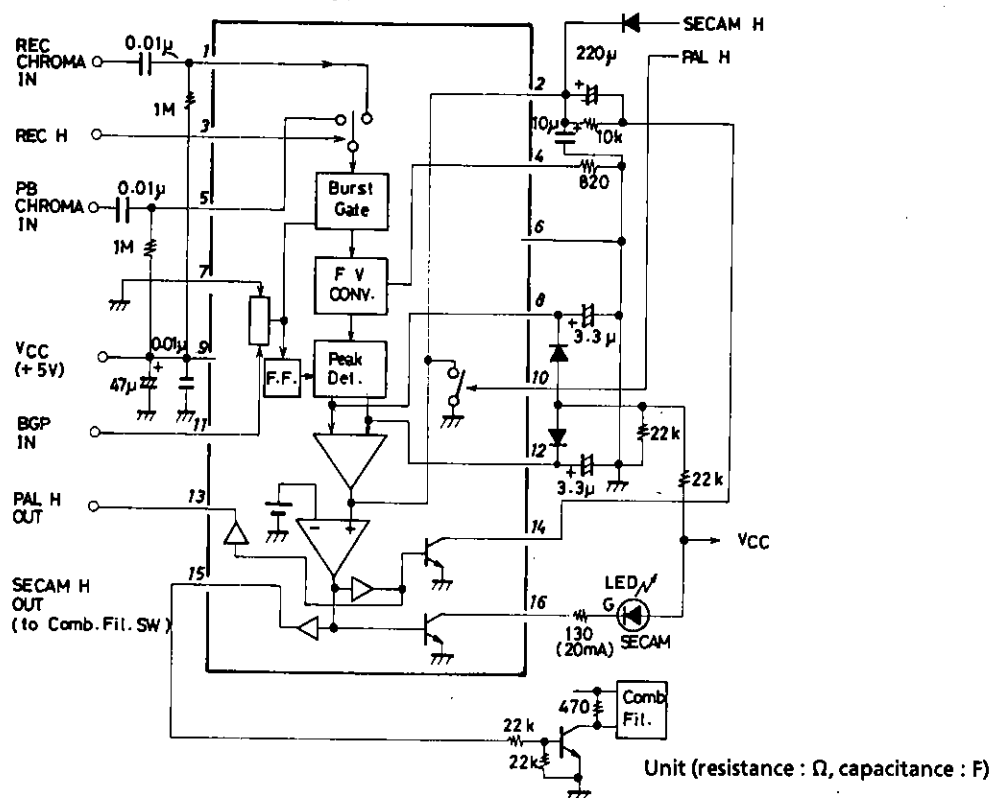
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

min	typ	max	unit
	0	5	μ A
	0	5	μ A
2.1	2.6	3.1	V
60	100	200	mV _{p-p}
	170	400	mV
	170	400	mV

The diagram shows a vacuum tube voltmeter (V7) circuit. It features a 6X4 vacuum tube (LA 7311) connected to a 250V filament. The circuit includes a 0.01μF capacitor, a 1MΩ resistor, and a 0.01μF capacitor. The input is connected to a 10μF capacitor and a 1MΩ resistor. The output is connected to a 10μF capacitor and a 1MΩ resistor. The circuit is powered by a 5V battery (+B) and a 5mA current source. The unit is labeled "Unit (resistance : Ω, capacitance : F)".

	S1	S2	S3	S4	S5	S6	Conditions
I _{CC}	off	off	off	off	off	off	V ₉ = 5V
ΔV _P	B	↓	↓	↓	↓	↓	100mV _{P-P} , difference between V ₈ (or V ₁₂) potential at 4.4MHz input and V ₈ (or V ₁₂) potential at 4.25MHz input
ΔV _R	A	on	↓	↓	↓	↓	100mV _{P-P} , difference between V ₈ (or V ₁₂) potential at 4.4MHz input and V ₈ (or V ₁₂) potential at 4.25MHz input
V ₈₋₁₂	off	off	↓	A	↓	↓	a (rise from 0) when V ₇ = 0V, V ₁₁ = 5V, V ₈ = 1.9V, V ₁₂ = 1.9V + a, V ₁₄ > 4V
V _{3TH}	↓	↓	↓	off	↓	↓	V ₃ (rise from 0) when V ₁ = V ₇ = V ₁₁ = 0V, V ₈ < 0.1V
V _{7TH}	↓	↓	↓	↓	↓	↓	V ₇ (rise from 0) when V ₁₁ = 5V, V ₈ > 1.0V
V _{11TH}	↓	↓	↓	↓	↓	↓	V ₁₁ (fall from 5V) when V ₇ = 0V, V ₈ > 1.0V
V _{10TH}	↓	↓	↓	↓	↓	A	V ₁₀ (rise from 0) when V ₇ = V ₁₁ = 0V, V ₁₆ > 4V
V _{2TH}	↓	↓	↓	A	↓	off	V ₂ (rise from 0) when V ₈ = V ₁₂ = 3V, V ₁₄ > 4V
V ₁₃	↓	↓	A	off	↓	↓	Pin 13 potential when V ₂ = 0V, drive current 5mA
V ₁₅	↓	↓	off	↓	A	↓	Pin 15 potential when V ₂ = 3V, drive current 5mA
I _{13(Leak)}	↓	↓	B	↓	off	↓	V ₂ = 3V, current which flows when pin 13 is connected to GND
I _{15(Leak)}	↓	↓	off	↓	B	↓	V ₂ = 0V, current which flows when pin 15 is connected to GND
V _{14(sat)}	↓	↓	↓	B	off	↓	Pin 14 potential when V ₂ = 0V, drive current 20mA
V _{16(sat)}	↓	↓	↓	off	↓	B	Pin 6 potential when V ₂ = 3V, drive current 20mA
V ₁₂	A	on	↓	↓	↓	off	100mV _{P-P} , 4.43MHz CW input, Apply 4μs $\overline{BGP}$ input to pin 11.
V _{IN}	A/B	on/off	↓	↓	↓	↓	

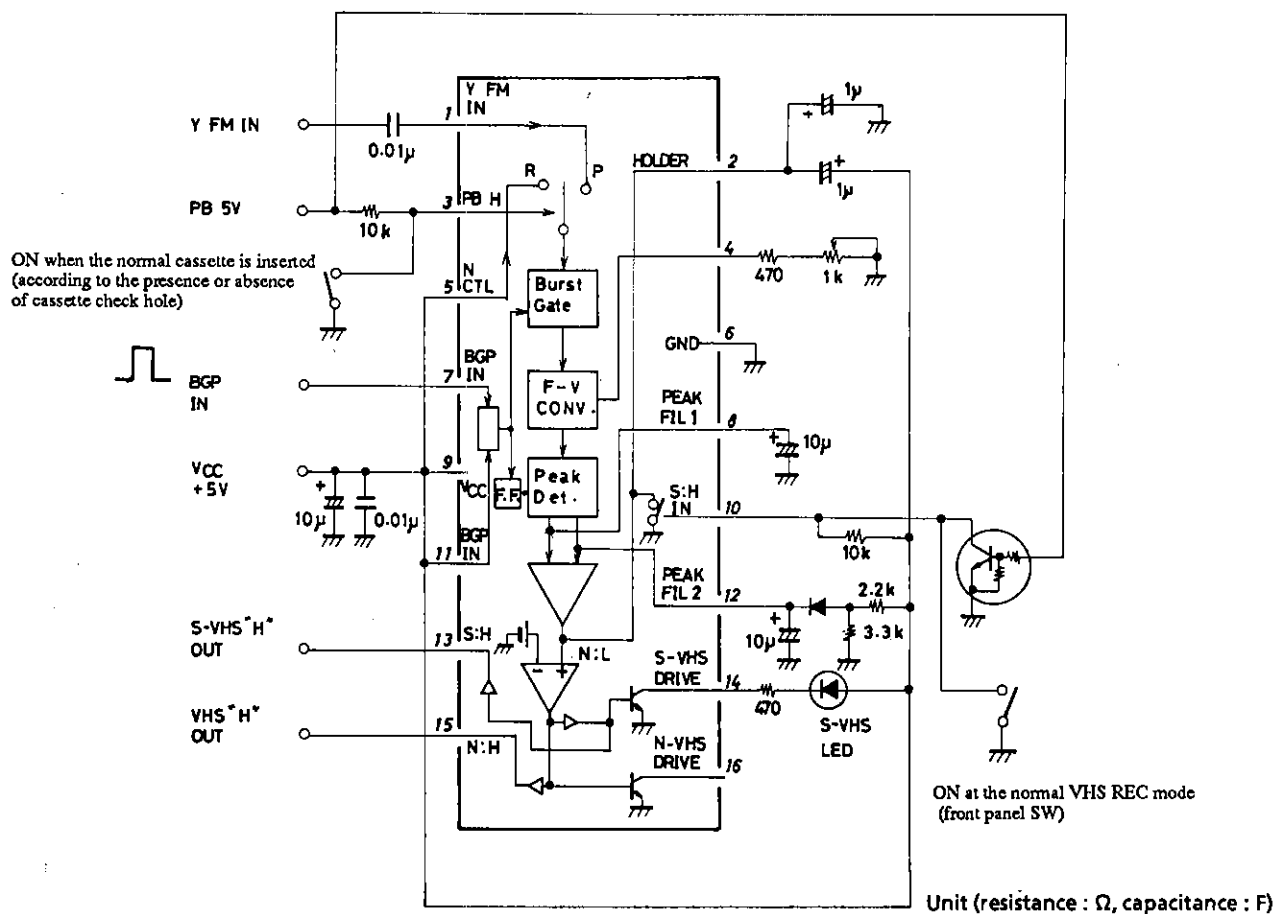
Equivalent Circuit Block Diagram and Sample Application Circuit (PAL/SECAM Discrimination)



Note 1: When the BGP is positive, apply an input to pin 7 and connect pin 11 to V_{CC}.

Note 2: When pin 10 is not in use, bring pin 10 to the open state or connect to GND.

Sample S-VHS Discriminator



Adjustment method: Adjust the VR (from VR center position) connected to pin 4 so that the DC voltage on pin 8 becomes 2.0V when the FM-Y signal at the (normal) VHS REC tape PB mode is input.

Note 1: When the BGP is negative, apply an input to pin 11 and connect pin 7 to GND.

Note 2: Pin 5 may be connected to GND.

Mode	Type of Cassette	Panel SW	V ₁₀	V ₂	Display
REC	N	S	H	L	S
		N	L	H	N
	S	S	H	L	S
		N	L	H	N
PB	N	S	L	H	N
		N	L	H	N
	S	S	L	Automatic discrimination	
		N	L	Automatic discrimination	

N; NORMAL VHS, S; S-VHS

Input/Output Configuration

Unit (resistance : Ω)

Pin	Pin Name	I/O Impedance or I/O Configuration	DC Voltage	Remarks
1	REC CHROMA IN	10k Ω	4.1V	
2	SECAM HOLDER			SECAM at 2.0V or greater
3	R/P CONTROL		0V (PB mode)	REC at 2.4V or greater
4	CURRENT SOURCE	Open emitter	410mV	
5	PB CHROMA IN	10k Ω	4.1V	
6	GND		0V	
7	BGP IN	Base		Burst gate at 1.7V or greater
8	PEAK FILTER 1	Emitter follower		
9	V _{CC}		5V	
10	PAL HIGH IN		0V	Forced PAL at 1.7V or greater
11	$\overline{\text{BGP}}$ IN	Base		Burst gate at 3.4V or less
12	PEAK FILTER 2	Emitter follower		
13	PAL HIGH OUT		4.1V (PAL mode)	Up to 5mA
14	PAL DRIVE	NPN open collector		Up to 25mA
15	SECAM HIGH OUT		4.1V (SECAM mode)	Up to 5mA
16	SECAM DRIVE	NPN open collector		Up to 25mA

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